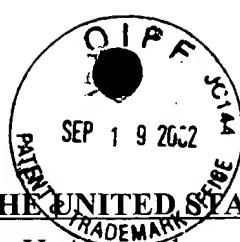


S/N 09/483,881



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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.
Serial No.: 09/483,881
Filed: January 18, 2000
Title: SELECTIVE ELECTROLESS-PLATED COPPER METALLIZATION

Examiner: Ha Nguyen
Group Art Unit: 2812
Docket: 303.672US1

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

This paper is in response to the Office Action mailed on June 14, 2002. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of previously pending claims 13, 19-21, 24, 28, 34, and 40, and addition of new claim 65. The specific amendments to individual claims are detailed in the following marked up set of claims.

13. (Amended) A method for forming copper vias and a first metal layer, comprising:
depositing a first seed layer including a thin film of Palladium (Pd) or Copper (Cu) on a substrate;

depositing a first patterned photoresist layer, wherein depositing the first patterned photoresist layer defines a first number of via holes above the first seed layer;

forming a first layer of copper using electroless plating, wherein forming the first layer of copper vias using electroless plating includes filling the first number of via holes to a top surface of the first patterned photoresist layer;

depositing a second seed layer including a thin film of Palladium (Pd) Copper (Cu) on the first layer of copper vias and the top surface of the photoresist layer;

depositing a second patterned photoresist layer, wherein depositing the second patterned photoresist layer defines a second number of conductor line openings above the second seed layer; and

forming a second layer of copper using electroless plating, wherein depositing a second

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